

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

SSM6J53FE

- High-Speed Switching Applications
- Power Management Switch Applications

Unit : mm

- 1.5 V drive
- Suitable for high-density mounting due to compact package
- Low on-resistance : $R_{on} = 136 \text{ m}\Omega$ (max) (@ $V_{GS} = -2.5 \text{ V}$)
 $R_{on} = 204 \text{ m}\Omega$ (max) (@ $V_{GS} = -1.8 \text{ V}$)
 $R_{on} = 364 \text{ m}\Omega$ (max) (@ $V_{GS} = -1.5 \text{ V}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	-20	V
Gate-Source voltage	V_{GSS}	± 8	V
Drain current	DC	I_D	A
	Pulse	I_{DP}	
Drain power dissipation	P_D (Note 1)	500	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

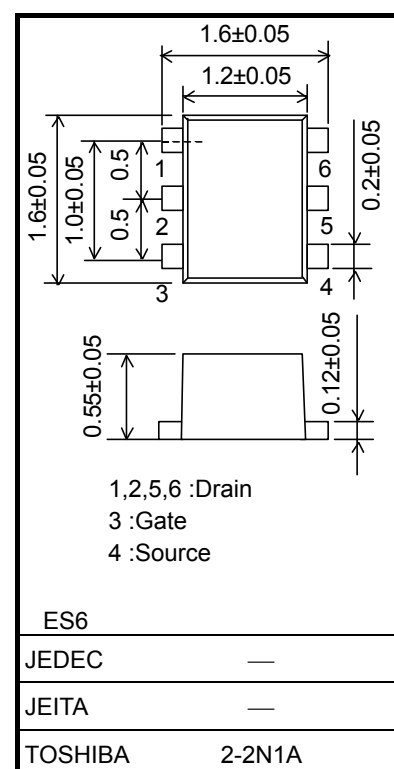
Note 1: Mounted on an FR4 board.

(25.4 mm $\times$ 25.4 mm $\times$ 1.6 t, Cu Pad: 645 mm²)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1 \text{ mA}, V_{GS} = 0$	-20	—	—	V
	$V_{(BR)DSX}$	$I_D = -1 \text{ mA}, V_{GS} = +8 \text{ V}$	-12	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0$	—	—	-10	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$	—	—	± 1	μA
Gate threshold voltage	V_{th}	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	-0.3	—	-1.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3 \text{ V}, I_D = -0.9 \text{ A}$ (Note 2)	2.7	5.4	—	S
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = -1.0 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note 2)	—	95	136	$\text{m}\Omega$
		$I_D = -1.0 \text{ A}, V_{GS} = -1.8 \text{ V}$ (Note 2)	—	122	204	
		$I_D = -0.1 \text{ A}, V_{GS} = -1.5 \text{ V}$ (Note 2)	—	137	364	
Input capacitance	C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$	—	568	—	pF
Output capacitance	C_{oss}		—	75	—	
Reverse transfer capacitance	C_{rss}		—	67	—	
Switching time	Turn-on time	$V_{DD} = -10 \text{ V}, I_D = -0.9 \text{ A}$ $V_{GS} = 0 \sim -2.5 \text{ V}, R_G = 4.7 \Omega$	—	29	—	ns
	Turn-off time		—	39	—	
Total gate charge	Q_g	$V_{DS} = -16 \text{ V}, I_{DS} = -1.8 \text{ A},$ $V_{GS} = -4 \text{ V}$	—	10.6	—	nC
Gate-Source charge	Q_{gs}		—	7.4	—	
Gate-Drain charge	Q_{gd}		—	3.3	—	
Drain-Source forward voltage	V_{DSF}	$I_D = 1.8 \text{ A}, V_{GS} = 0$ (Note 2)	—	0.8	1.2	V

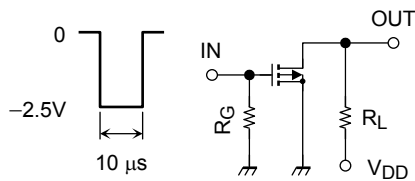
Note 2: Pulse test



Weight: 7.0 mg (typ.)

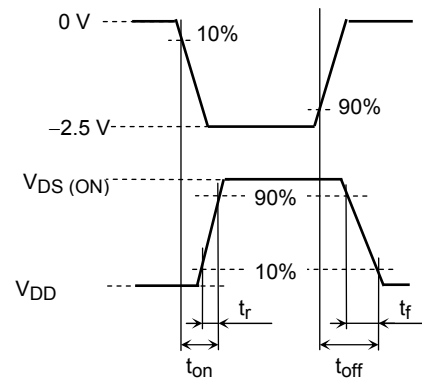
Switching Time Test Circuit

(a) Test Circuit

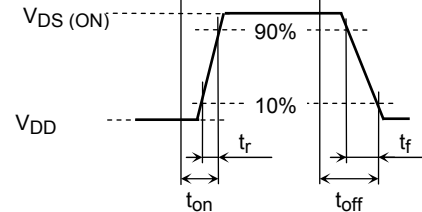


$V_{DD} = -10\text{ V}$
 $R_G = 4.7\ \Omega$
 $D.U. \leq 1\%$
 $V_{IN}: t_r, t_f < 5\text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

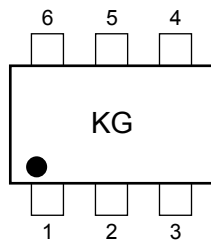
(b) V_{IN}



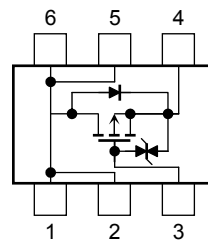
(c) V_{OUT}



Marking



Equivalent Circuit (top view)



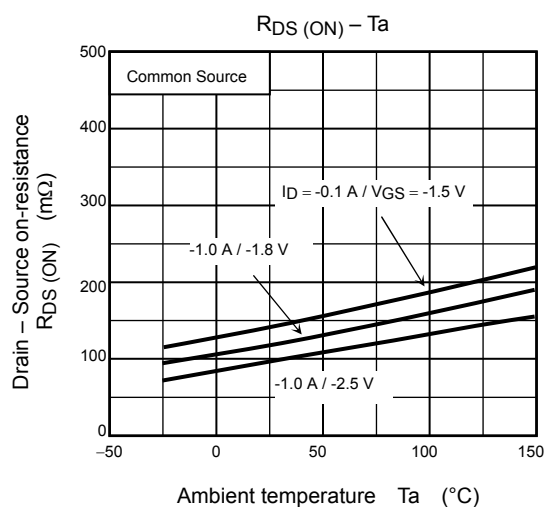
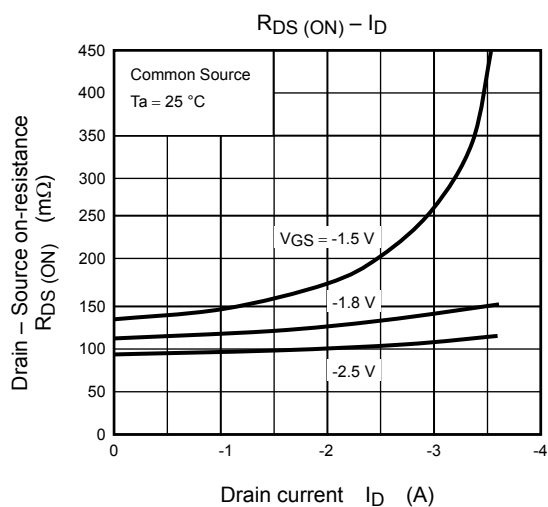
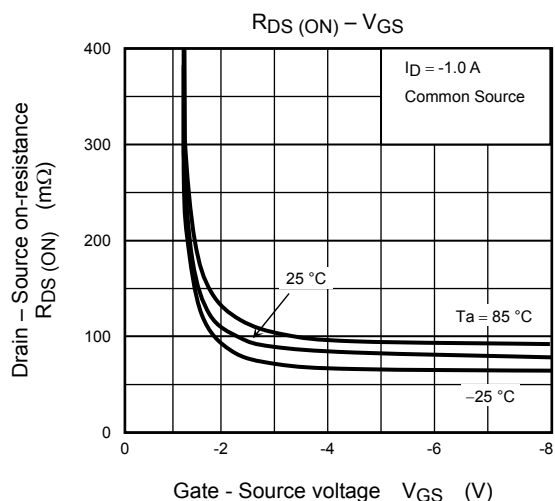
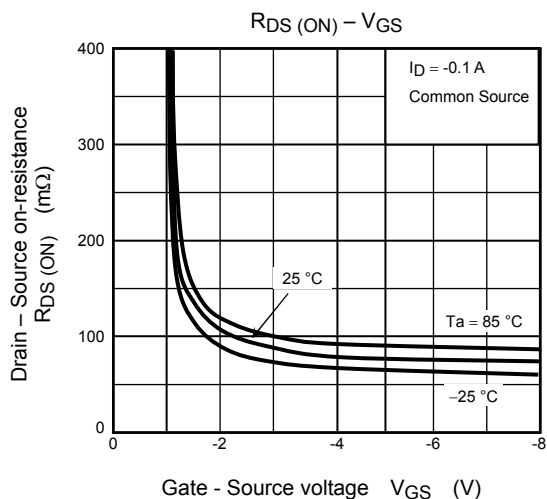
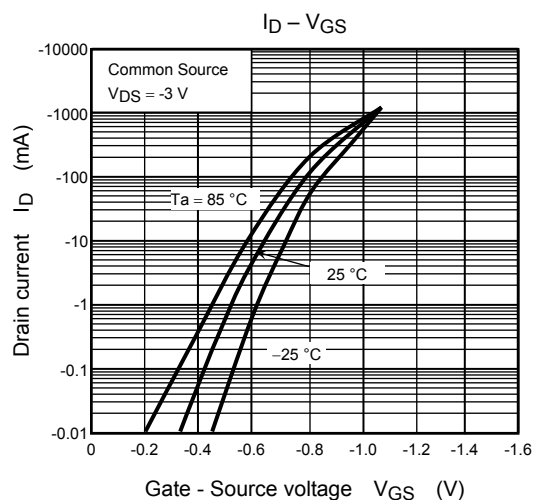
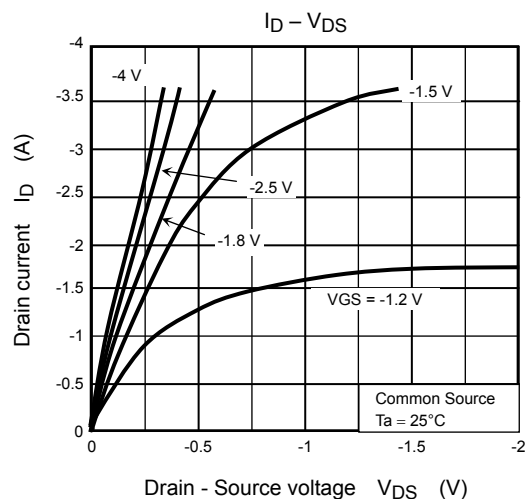
Precaution

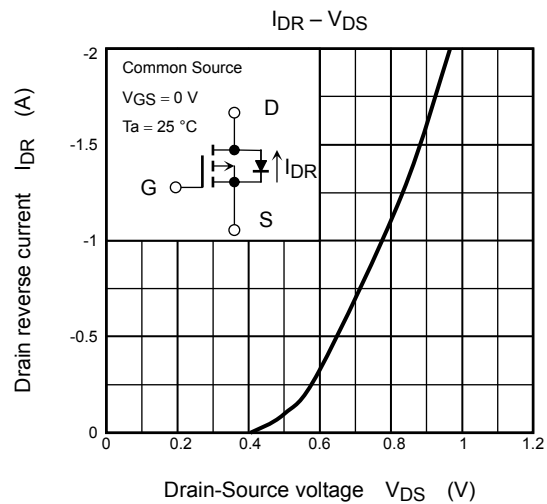
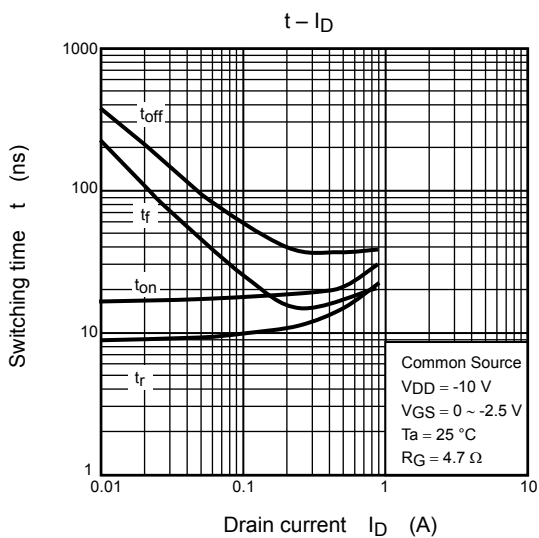
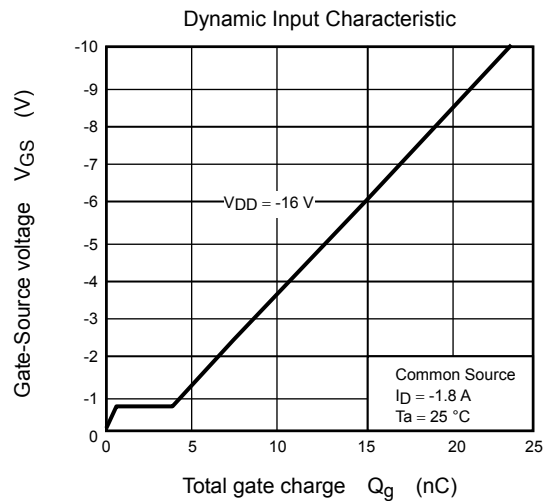
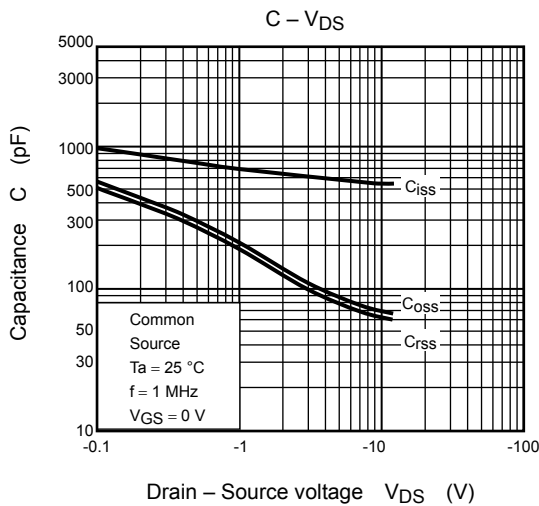
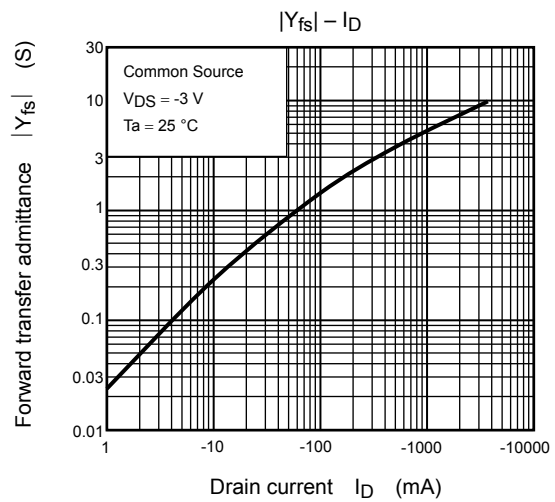
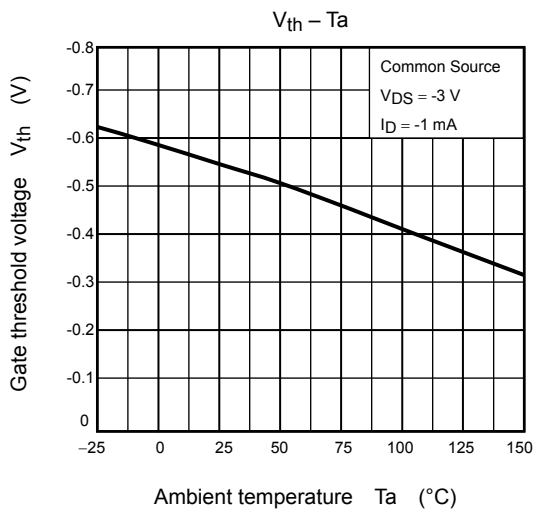
V_{th} can be expressed as the voltage between the gate and source when the low operating current value is $I_D = -1\text{mA}$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} and $V_{GS(off)}$ requires a lower voltage than V_{th} . (The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$.)

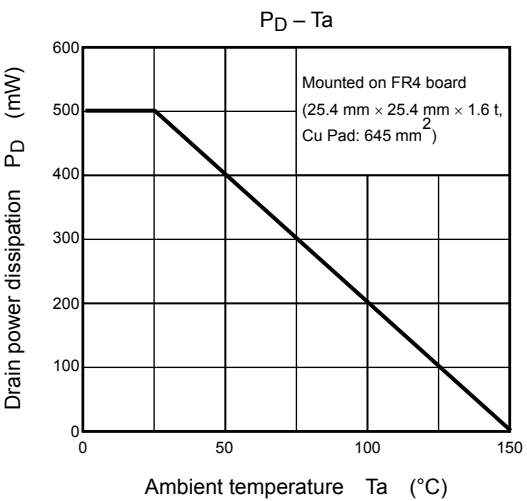
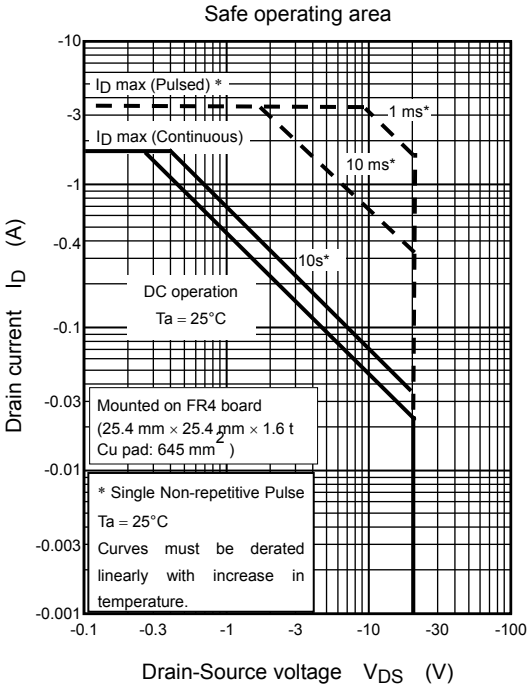
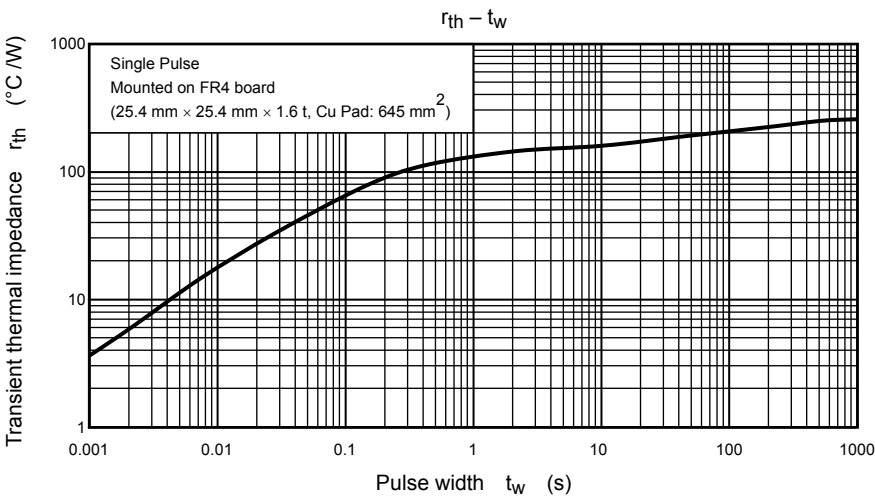
Be sure to take this into consideration when using the device.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.







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20070701-EN GENERAL

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